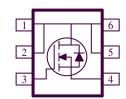
## N-Channel 60V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, cellular and cordless telephones.

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$V_{DS}(V)$ $r_{DS(on)}(\Omega)$				
60	$0.027 @ V_{GS} = 10 V$	7.1			
	$0.033 @ V_{GS} = 4.5V$	6.4			

- $\begin{tabular}{ll} \bullet & Low \ r_{DS(on)} \ provides \ higher \ efficiency \ and \\ extends \ battery \ life \end{tabular}$
- Low thermal impedance copper leadframe TSOP-6 saves board space
- Fast switching speed
- High performance trench technology





RoHS
COMPLIANT
HALOGEN
FRFF

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)						
Parameter			<b>Maximum Units</b>			
Drain-Source Voltage			60	V		
Gate-Source Voltage			±20	V		
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	Τ_	7.1			
Continuous Drain Current	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	П	5.8	A		
Pulsed Drain Current <sup>b</sup>			±15			
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	1.7	A			
D a	$T_A=25^{\circ}C$	$P_{\mathrm{D}}$	2.0	W		
Power Dissipation <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	rD	1.3			
Operating Junction and Storage Temperature Range			-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
M · I · · a	t <= 5 sec	D	62.5	°C/W		
Maximum Junction-to-Ambient <sup>a</sup>	Steady-State	$R_{THJA}$	110			

1

## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Analog Power AM3460N

SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)								
Devices Asia	G 1.1	T C W.	Limits			<b>T</b> T •4		
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit		
Static								
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	1			V		
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$			1	uА		
Zeio Gate Voltage Diam Current	IDSS	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$	$= 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$ 50			¬ uA		
On-State Drain Current <sup>A</sup>	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	10			A		
D : C C D : A	fDS(on)	$V_{GS} = 10 \text{ V}, I_D = 1 \text{ A}$			27	mΩ		
Drain-Source On-Resistance <sup>A</sup>		$V_{GS} = 4.5 \text{ V}, I_D = 1 \text{ A}$			33			
Forward Tranconductance <sup>A</sup>	gfs	$V_{DS} = 4.5 \text{ V}, I_D = 1 \text{ A}$		8		S		
Diode Forward Voltage	V <sub>SD</sub>	$I_S = 1 A, V_{GS} = 0 V$		1.1		V		
Dynamic <sup>b</sup>								
Total Gate Charge	Qg			9		nC		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 30 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 1 \text{ A}$		2				
Gate-Drain Charge	$Q_{\mathrm{gd}}$			3		1		
Turn-On Delay Time	t <sub>d(on)</sub>			5				
Rise Time	t <sub>r</sub>	$V_{DD} = 30 \; V,  R_L = 30 \; \Omega,  I_D = 1 \; A, $		6				
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{\rm GEN} = 10 \ { m V}$		30		ns		
Fall-Time	t <sub>f</sub>			9		Ī		

## Notes

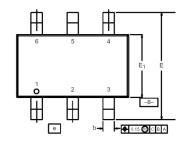
- a. Pulse test:  $PW \le 300$ us duty cycle  $\le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

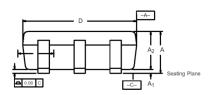
Analog Power (APL) reserves the right to make changes without further notice to any products herein. APL makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does APL assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in APL data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. APL does not convey any license under its patent rights nor the rights of others. APL products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the APL product could create a situation where personal injury or death may occur. Should Buyer purchase or use APL products for any such unintended or unauthorized application, Buyer shall indemnify and hold APL and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that APL was negligent regarding the design or manufacture of the part. APL is an Equal Opportunity/Affirmative Action Employer.

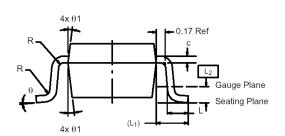
Analog Power AM3460N

## Package Information

TSOP-6: 6LEAD







	MILLIMETERS INCHES			<b>;</b>		
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.91	_	1.10	0.036	_	0.043
A <sub>1</sub>	0.01	_	0.10	0.0004	-	0.004
A <sub>2</sub>	0.84	_	1.00	0.033	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
С	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067
е	1.00 BSC			0.0394 BSC		
L	0.35	_	0.50	0.014	-	0.020
L <sub>1</sub>		0.60 Ref 0.024 Ref				
L <sub>2</sub>	0.25 BSC				0.010 BSC	
R	0.10	_	_	0.004	-	_
θ	0°	4°	8°	0°	4°	8°
$\theta_1$	7° Nom				7° Nom	